Ahmad Zubair

List of Publications by Year in descending order

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18 papers	2,466 citations	567281 15 h-index	888059 17 g-index
19 all docs	19 docs citations	19 times ranked	4621 citing authors

#	Article	IF	Citations
1	Antiferroelectric negative capacitance from a structural phase transition in zirconia. Nature Communications, 2022, 13, 1228.	12.8	22
2	GaN FinFETs and trigate devices for power and RF applications: review and perspective. Semiconductor Science and Technology, 2021, 36, 054001.	2.0	59
3	GaN 2.0: Power FinFETs, Complementary Gate Drivers and Low-Cost Vertical Devices. , 2021, , .		7
4	WSe₂/graphene heterojunction synaptic phototransistor with both electrically and optically tunable plasticity. 2D Materials, 2021, 8, 035034.	4.4	17
5	Impact of Al₂O₃ Passivation on the Photovoltaic Performance of Vertical WSe₂ Schottky Junction Solar Cells. ACS Applied Materials & Interfaces, 2020, 12, 57987-57995.	8.0	19
6	Two-dimensional MoS2-enabled flexible rectenna for Wi-Fi-band wireless energy harvesting. Nature, 2019, 566, 368-372.	27.8	266
7	Paraffin-enabled graphene transfer. Nature Communications, 2019, 10, 867.	12.8	185
8	Negative Capacitance Carbon Nanotube FETs. IEEE Electron Device Letters, 2018, 39, 304-307.	3.9	39
9	Large Area 1.2 kV GaN Vertical Power FinFETs with a Record Switching Figure-of-Merit. IEEE Electron Device Letters, 2018, , 1-1.	3.9	69
10	Hot Electron Transistor with van der Waals Base-Collector Heterojunction and High-Performance GaN Emitter. Nano Letters, 2017, 17, 3089-3096.	9.1	74
11	Subthreshold swing improvement in MoS₂ transistors by the negative-capacitance effect in a ferroelectric Al-doped-HfO₂/HfO₂ gate dielectric stack. Nanoscale, 2017, 9, 6122-6127.	5.6	123
12	Role of Molecular Sieves in the CVD Synthesis of Largeâ€Area 2D MoTe ₂. Advanced Functional Materials, 2017, 27, 1603491.	14.9	58
13	Synthesis of Highâ€Quality Largeâ€Area Homogenous 1Tâ€² MoTe₂ from Chemical Vapor Deposition. Advanced Materials, 2016, 28, 9526-9531.	21.0	125
14	MoS₂ Field-Effect Transistor with Sub-10 nm Channel Length. Nano Letters, 2016, 16, 7798-7806.	9.1	389
15	A Rational Strategy for Graphene Transfer on Substrates with Rough Features. Advanced Materials, 2016, 28, 2382-2392.	21.0	78
16	Transport Properties of a MoS₂/WSe₂ Heterojunction Transistor and Its Potential for Application. Nano Letters, 2016, 16, 1359-1366.	9.1	430
17	High-Performance WSe₂ Complementary Metal Oxide Semiconductor Technology and Integrated Circuits. Nano Letters, 2015, 15, 4928-4934.	9.1	204
18	Large-Area Synthesis of High-Quality Uniform Few-Layer MoTe₂. Journal of the American Chemical Society, 2015, 137, 11892-11895.	13.7	302